

Fig. 1

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ZnO thickness ~ 500 nm/Si

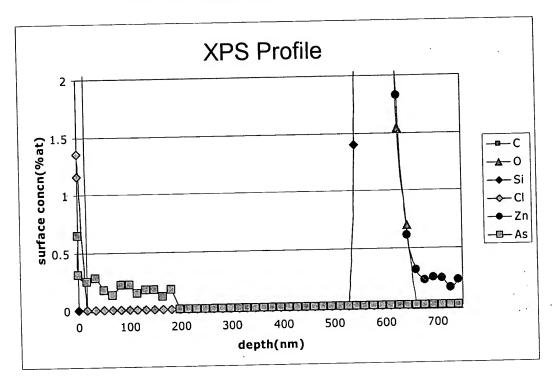


Fig. 2

Docket No.: 3398.2.8

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P-type ZnO: Photoluminescent Comparisons

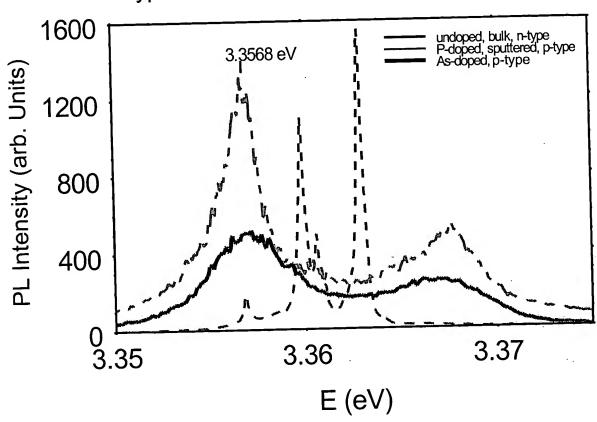


Fig. 3

Docket No.: 3398.2.8

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Resistance & Mobility of As doped ZnO

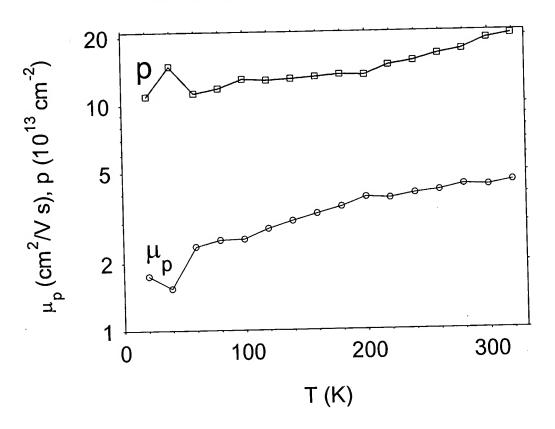


Fig. 4

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SIMS Data Showing Concentration vs. Depth

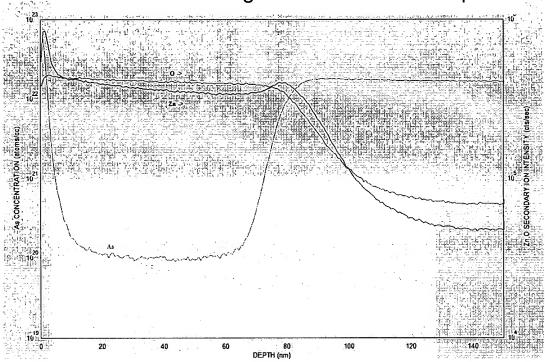


Fig. 5

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Polycrystalline Zinc Oxide XRD Pattern

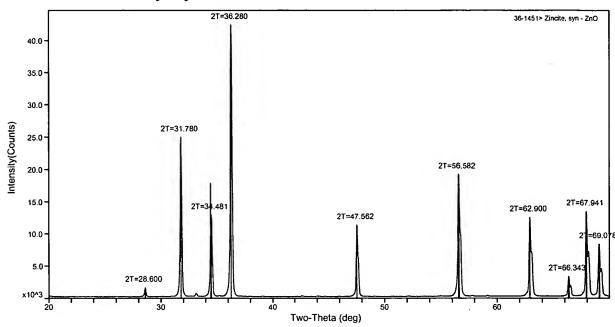


Fig. 6

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Zinc Oxide XRD Pattern Showing Single Crystal (002) Plane

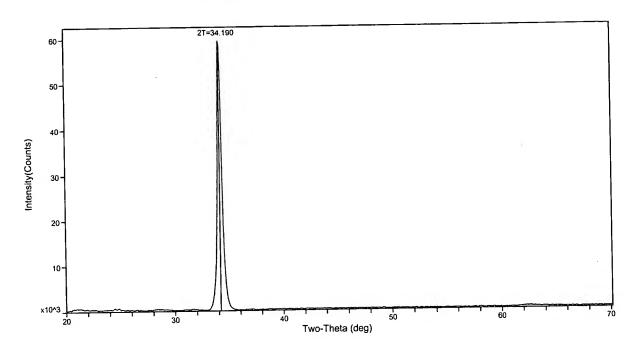


Fig. 7

Title: FABRICATION OF P-TYPE GROUP II-VI SEMICONDUCTORS

Inventors: Robert H. Burgener, II et al. Docket No.: 3398.2.8

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Antimony Concentration In Zinc Oxide Atoms/cm³ verses Depth Into The Surface

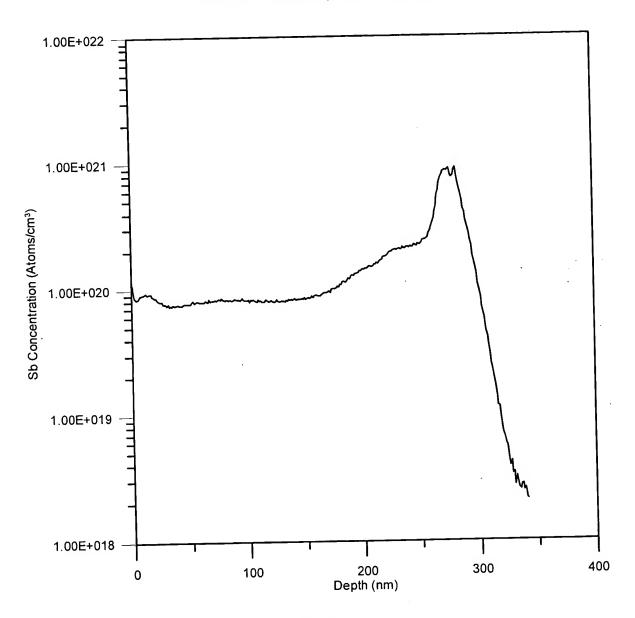


Fig. 8

Docket No.: 3398.2.8

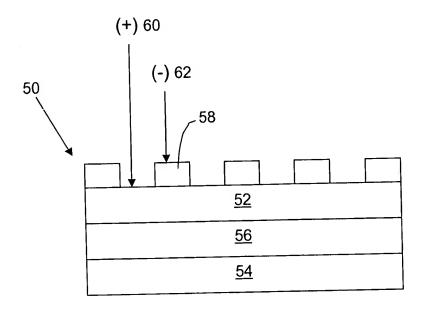


Fig. 9

Title: FABRICATION OF P-TYPE GROUP II-VI SEMICONDUCTORS

Inventors: Robert H. Burgener, II et al. Docket No.: 3398.2.8

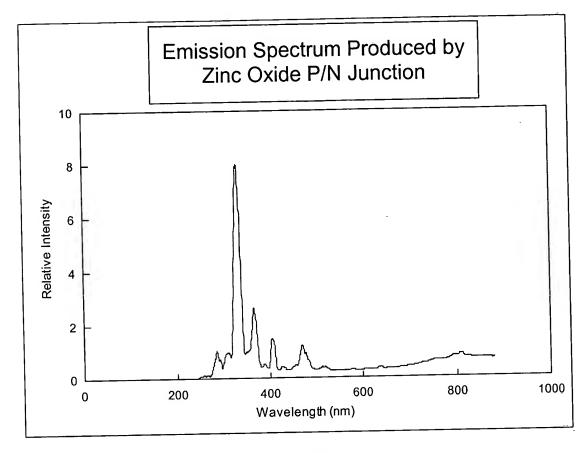


Fig. 10

Current - Voltage Plot of a Zinc Oxide P/N Junction

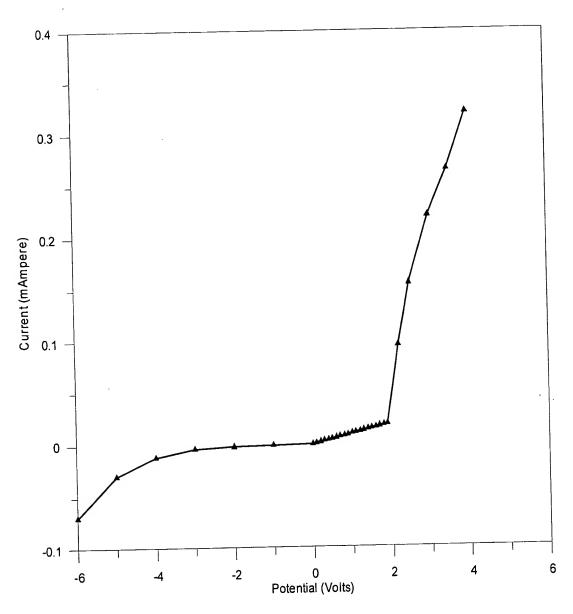


Fig. 11

Title: FABRICATION OF P-TYPE GROUP II-VI SEMICONDUCTORS

Inventors: Robert H. Burgener, II et al. Docket No.: 3398.2.8

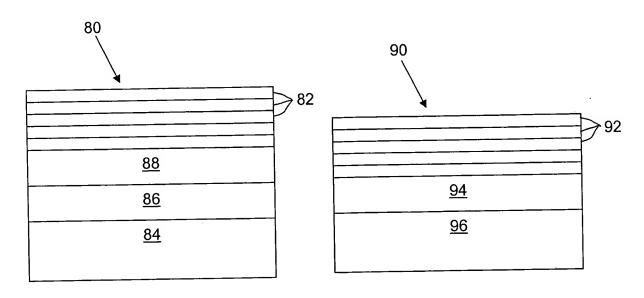


Fig. 12A

Fig. 12B

Zinc - Oxygen - Arsenic Ternary Diagram

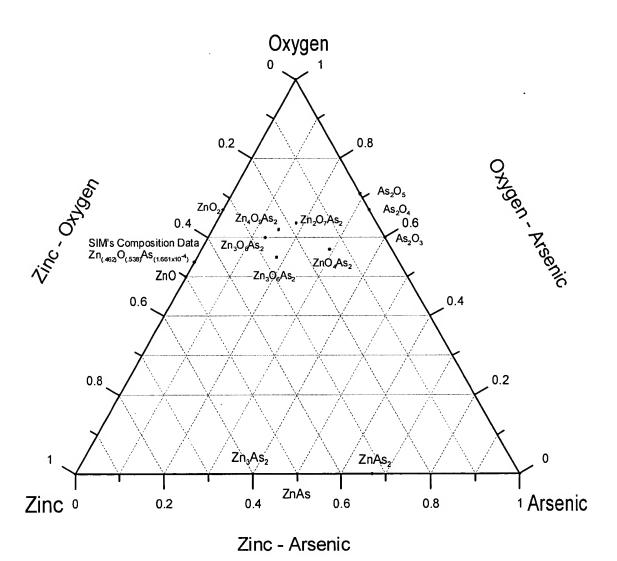


Fig. 13